UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,951,805 B2
APPLICATION NO. : 09/921,518
DATED : October 4, 2005
INVENTOR(S) : John T. Moore

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 3, line 56, "spacers 29" should read --spacers 30--.

TITLE Pg. ITEM (56)

In the Other Publications portion of the References Cited section the following errors are corrected:

"Alekperova, Sh.M.; Gadshleva, G.S., Current-Voltage characteristics of Ag_2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139."

Should read

--Alekperova, Sh.M.; Gadzhieva, G.S., Current-voltage characteristics of Ag_2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.--;

"Aleksiejunas, A.; Cesnys, A., Swithcing phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19(1973) K169-171."

Should read

--Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19(1973) K169-171.--;

"Boolchand, P.; Basser, W.J. Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073."

Should read

--Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.--;

"Gates, B.; Wu, Y.; Yang. P.; Xia, Y., Single-crystalline nanowires of Ag_2Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP."

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--Gates, B.; Wu, Y.; Yin, Y.; Yang. P.; Xia, Y., Single-crystalline nanowires of Ag_2Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.--;

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"Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1998) 825-828."

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"Kawaguchi, T.; Masui, K., Analysis of chang in optical transmission spectra resulting from Ag photodoping in chalcogenid film, Japan J. Appl. Phys. 26 (1987) 15-21."

Should read

--Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Japan J. Appl. Phys. 26 (1987) 15-21.--;

"Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect f topology on lectrical switching in chalcogenid network glasses, Phys. Rev. B 54 (1996) 4413-4415."

Should read

--Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses, Phys. Rev. B 54 (1996) 4413-4415.--;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Siver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso Internatioanl symposium, Sep. 9-13, 1985."

Should read

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985.--;

"Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally Induced crystallization of amorphous $Ge_{0.4}Se_{0.6}$, J. Non-Cryst. Solids 117-118 (1990) 219-221.".

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"West, W.C.; Sleradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the $Ag|As_{0.24}S_{0.36}Ag_{0.40}|Ag$ System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974."

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--West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the $Ag|As_{0.24}S_{0.36}Ag_{0.40}|Ag$ System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.--;

"Yoji Kawamoto et al., "Ionic Conduction in As_2S_3-$Ag_2S_1GeS_2$-GeS+- Ag_2S and P_2S_5-Ag_2S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404."

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--Yoji Kawamoto et al., "Ionic Conduction in As_2S_3-$Ag_2S_1GeSe_2$-GeS- Ag_2S and P_2S_5-Ag_2S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.--; and

"Miyatani, *Electrical Porperties of Ag_2Se*, 13 J. Phys. Soc. Japan, p. 317 (1958)."

Should read

--Miyatani, *Electrical Properties of Ag_2Se*, 13 J. Phys. Soc. Japan, p.317

Signed and Sealed this

Fifteenth Day of August, 2006

JON W. DUDAS
Director of the United States Patent and Trademark Office